
R1LV0108E Series

1Mb Advanced LPSRAM (128k word x 8bit)

R10DS0152EJ0100
Rev.1.00
2013.6.21

Description

The R1LV0108E Series is a family of low voltage 1-Mbit static RAMs organized as 131,072-word by 8-bit, fabricated by Renesas's high-performance 0.15um CMOS and TFT technologies. The R1LV0108E Series has realized higher density, higher performance and low power consumption. The R1LV0108E Series is suitable for memory applications where a simple interfacing, battery operating and battery backup are the important design objectives. It has been packaged in 32-pin SOP, 32-pin TSOP and 32-pin sTSP.

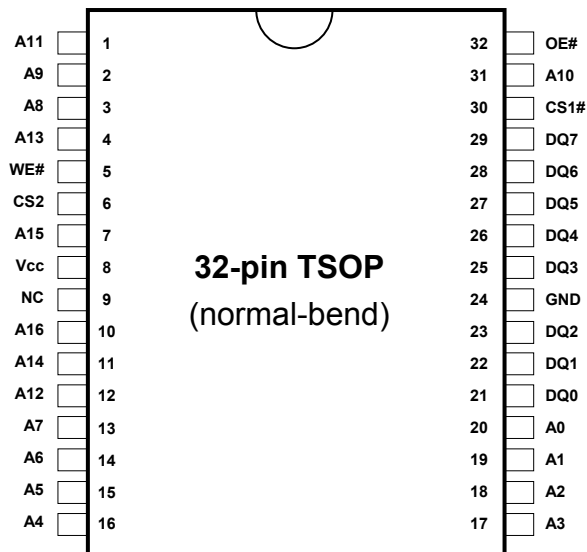
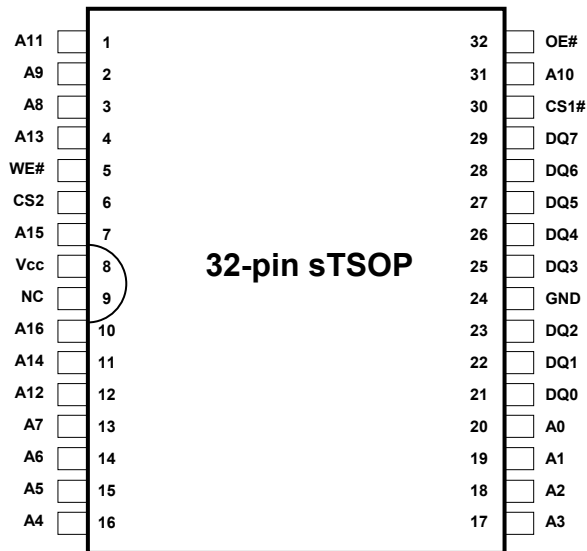
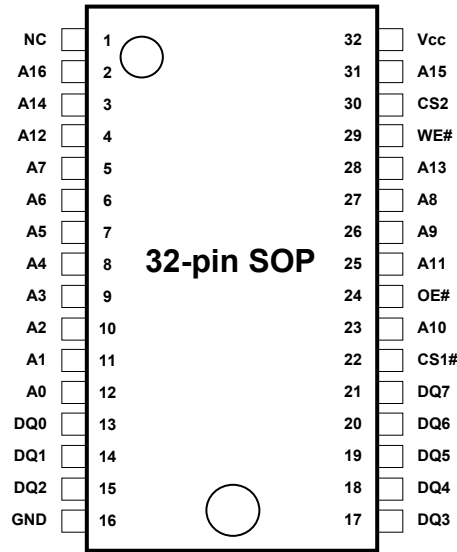
Features

- Single 2.7~3.6V power supply
- Small stand-by current: 0.6μA (3.0V, typical)
- No clocks, No refresh
- All inputs and outputs are TTL compatible.
- Easy memory expansion by CS1# and CS2
- Common Data I/O
- Three-state outputs: OR-tie Capability
- OE# prevents data contention on the I/O bus

Ordering Information

Orderable Part Name	Access time	Temperature Range	Package	Shipping Container	Quantity
R1LV0108ESN-5SR#B*	55 ns	0 ~ +70°C	525-mil 32-pin plastic SOP	Tube	Max. 25pcs/Tube Max. 225pcs/Inner Bag Max. 900pcs/Inner Box
R1LV0108ESN-5SI#B*		-40 ~ +85°C			
R1LV0108ESN-7SR#B*	70 ns	0 ~ +70°C			
R1LV0108ESN-7SI#B*		-40 ~ +85°C			
R1LV0108ESN-5SR#S*	55 ns	0 ~ +70°C	PRSP0032DF-A (32P2S-A)	Embossed tape	1000pcs/Reel
R1LV0108ESN-5SI#S*		-40 ~ +85°C			
R1LV0108ESN-7SR#S*	70 ns	0 ~ +70°C			
R1LV0108ESN-7SI#S*		-40 ~ +85°C			
R1LV0108ESA-5SR#B*	55 ns	0 ~ +70°C	8mm×13.4mm 32-pin plastic sT SOP (normal-bend type)	Tray	Max. 234pcs/Tray Max. 1872pcs/Inner Box
R1LV0108ESA-5SI#B*		-40 ~ +85°C			
R1LV0108ESA-7SR#B*	70 ns	0 ~ +70°C			
R1LV0108ESA-7SI#B*		-40 ~ +85°C			
R1LV0108ESA-5SR#S*	55 ns	0 ~ +70°C	PTSA0032KB-A (32P3K-B)	Embossed tape	1000pcs/Reel
R1LV0108ESA-5SI#S*		-40 ~ +85°C			
R1LV0108ESA-7SR#S*	70 ns	0 ~ +70°C			
R1LV0108ESA-7SI#S*		-40 ~ +85°C			
R1LV0108ESF-5SR#B*	55 ns	0 ~ +70°C	8mm×20mm 32-pin plastic TSOP (normal-bend type)	Tray	Max. 156pcs/Tray Max. 1248pcs/Inner Box
R1LV0108ESF-5SI#B*		-40 ~ +85°C			
R1LV0108ESF-7SR#B*	70 ns	0 ~ +70°C			
R1LV0108ESF-7SI#B*		-40 ~ +85°C			
R1LV0108ESF-5SR#S*	55 ns	0 ~ +70°C	PTSA0032KA-A (32P3H-E)	Embossed tape	1000pcs/Reel
R1LV0108ESF-5SI#S*		-40 ~ +85°C			
R1LV0108ESF-7SR#S*	70 ns	0 ~ +70°C			
R1LV0108ESF-7SI#S*		-40 ~ +85°C			

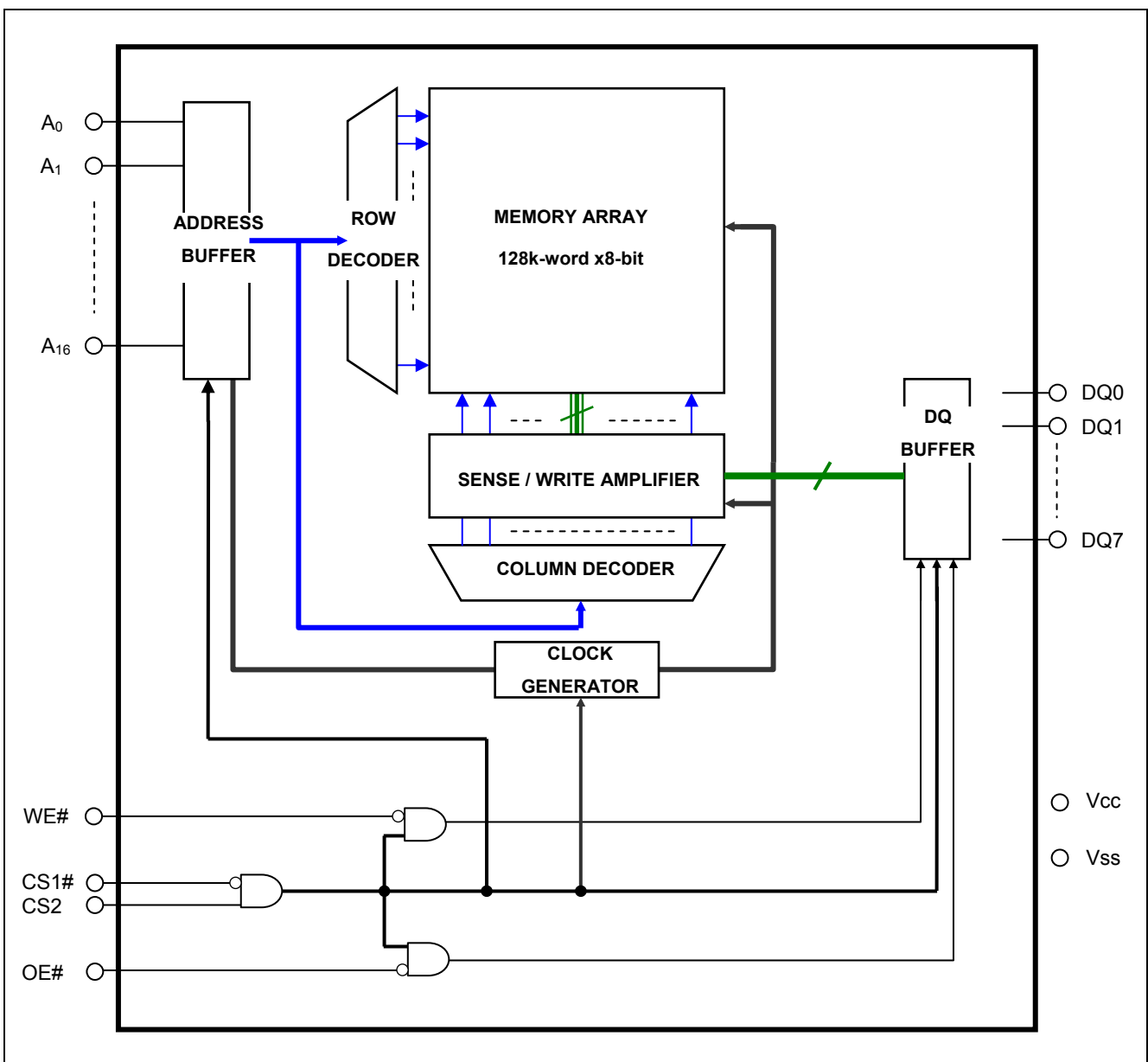
Pin Arrangement



Pin Description

Pin name	Function
Vcc	Power supply
Vss	Ground
A0 to A16	Address input
DQ0 to DQ7	Data input/output
CS1#	Chip select 1
CS2	Chip select 2
WE#	Write enable
OE#	Output enable
NC	Non connection

Block Diagram



Operation Table

CS1#	CS2	WE#	OE#	DQ0~7	Operation
X	L	X	X	High-Z	Stand-by
H	X	X	X	High-Z	Stand-by
L	H	L	X	Din	Write
L	H	H	L	Dout	Read
L	H	H	H	High-Z	Output disable

Note 1. H: V_{IH} L: V_{IL} X: V_{IH} or V_{IL}

Absolute Maximum

Parameter	Symbol	Value	unit
Power supply voltage relative to Vss	Vcc	-0.3 to +4.6	V
Terminal voltage on any pin relative to Vss	V_T	-0.3^{*1} to $V_{cc}+0.3^{*2}$	V
Power dissipation	P_T	0.7	W
Operation temperature	T_{opr}^{*3}	R Ver.	0 to +70
		I Ver.	-40 to +85
Storage temperature range	T_{stg}	-65 to 150	°C
Storage temperature range under bias	T_{bias}^{*3}	R Ver.	0 to +70
		I Ver.	-40 to +85

- Note
1. -3.0V for pulse ≤ 30 ns (full width at half maximum)
 2. Maximum voltage is +4.6V.
 3. Ambient temperature range depends on R/I-version. Please see table on page 1.

DC Operating Conditions

Parameter	Symbol	Min.	Typ.	Max.	Unit	Note	
Supply voltage	V _{CC}	2.7	3.0	3.6	V		
	V _{SS}	0	0	0	V		
Input high voltage	V _{IH}	2.0	-	V _{CC} +0.3	V		
Input low voltage	V _{IL}	-0.3	-	0.6	V	1	
Ambient temperature range	R Ver.	T _a	0	-	+70	°C	2
	I Ver.		-40	-	+85	°C	2

- Note 1. -3.0V for pulse ≤ 30ns (full width at half maximum)
 2. Ambient temperature range depends on R/I-version. Please see table on page 1.

DC Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test conditions	
Input leakage current	I _{LI}	-	-	1	μA	V _{in} = V _{SS} to V _{CC}	
Output leakage current	I _{LO}	-	-	1	μA	CS1# = V _{IH} or CS2 = V _{IL} or OE# = V _{IH} , V _{I/O} = V _{SS} to V _{CC}	
Average operating current	I _{CC1}	-	15	25	mA	Min. cycle, duty = 100%, I _{I/O} = 0mA CS1# = V _{IL} , CS2 = V _{IH} , Others = V _{IH} /V _{IL}	
	I _{CC2}	-	2	5	mA	Cycle = 1μs, duty = 100%, I _{I/O} = 0mA CS1# ≤ 0.2V, CS2 ≥ V _{CC} -0.2V, V _{IH} ≥ V _{CC} -0.2V, V _{IL} ≤ 0.2V	
Standby current	I _{SB}	-	-	0.33	mA	"CS2 = V _{IL} " or "CS2 = V _{IH} and CS1# = V _{IH} ", Others = V _{SS} to V _{CC}	
Standby current	I _{SB1}	-	0.6 ^{*1}	2	μA	~+25°C	V _{in} = V _{SS} to V _{CC} (1) CS2 ≤ 0.2V or (2) CS1# ≥ V _{CC} -0.2V, CS2 ≥ V _{CC} -0.2V
		-	-	3	μA	~+40°C	
		-	-	8	μA	~+70°C	
		-	-	10	μA	~+85°C	
Output high voltage	V _{OH}	2.4	-	-	V	I _{OH} = -0.5mA	
	V _{OH2}	V _{CC} - 0.5	-	-	V	I _{OH} = -0.05mA	
Output low voltage	V _{OL}	-	-	0.4	V	I _{OL} = 2mA	

- Note 1. Typical parameter indicates the value for the center of distribution at 3.0V (T_a = 25°C), and not 100% tested.

Capacitance

(V_{CC} = 2.7V ~ 3.6V, f = 1MHz, T_a = 0 ~ +70°C / -40 ~ +85°C^{*2})

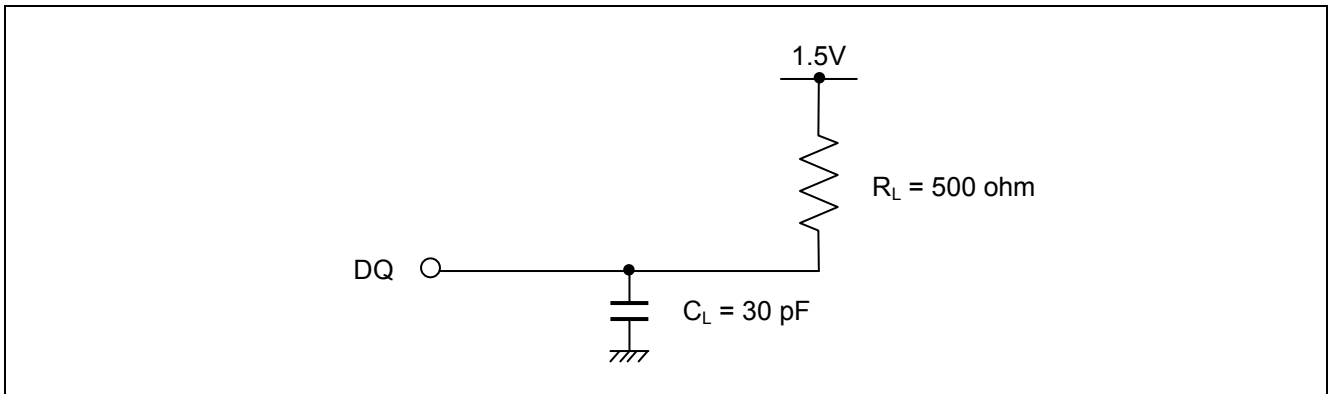
Parameter	Symbol	Min.	Typ.	Max.	Unit	Test conditions	Note
Input capacitance	C _{in}	-	-	8	pF	V _{in} = 0V	1
Input / output capacitance	C _{I/O}	-	-	10	pF	V _{I/O} = 0V	1

- Note 1. This parameter is sampled and not 100% tested.
 2. Ambient temperature range depends on R/I-version. Please see table on page 1.

AC Characteristics

Test Conditions ($V_{CC} = 2.7V \sim 3.6V$, $T_a = 0 \sim +70^{\circ}C / -40 \sim +85^{\circ}C^{*1}$)

- Input pulse levels: $V_{IL} = 0.4V$, $V_{IH} = 2.2V$
- Input rise and fall time: 5ns
- Input and output timing reference level: 1.5V
- Output load: See figures (Including scope and jig)



Note 1. Ambient temperature range depends on R/I-version. Please see table on page 1.

Read Cycle

Parameter	Symbol	R1LV0108E**-5**		R1LV0108E**-7**		Unit	Note
		Min.	Max.	Min.	Max.		
Read cycle time	t_{RC}	55	-	70	-	ns	
Address access time	t_{AA}	-	55	-	70	ns	
Chip select access time	t_{ACS1}	-	55	-	70	ns	
	t_{ACS2}	-	55	-	70	ns	
Output enable to output valid	t_{OE}	-	30	-	35	ns	
Output hold from address change	t_{OH}	5	-	10	-	ns	
Chip select to output in low-Z	t_{CLZ1}	5	-	10	-	ns	2,3
	t_{CLZ2}	5	-	10	-	ns	2,3
Output enable to output in low-Z	t_{OLZ}	5	-	5	-	ns	2,3
Chip deselect to output in high-Z	t_{CHZ1}	0	20	0	25	ns	1,2,3
	t_{CHZ2}	0	20	0	25	ns	1,2,3
Output disable to output in high-Z	t_{OHZ}	0	20	0	25	ns	1,2,3

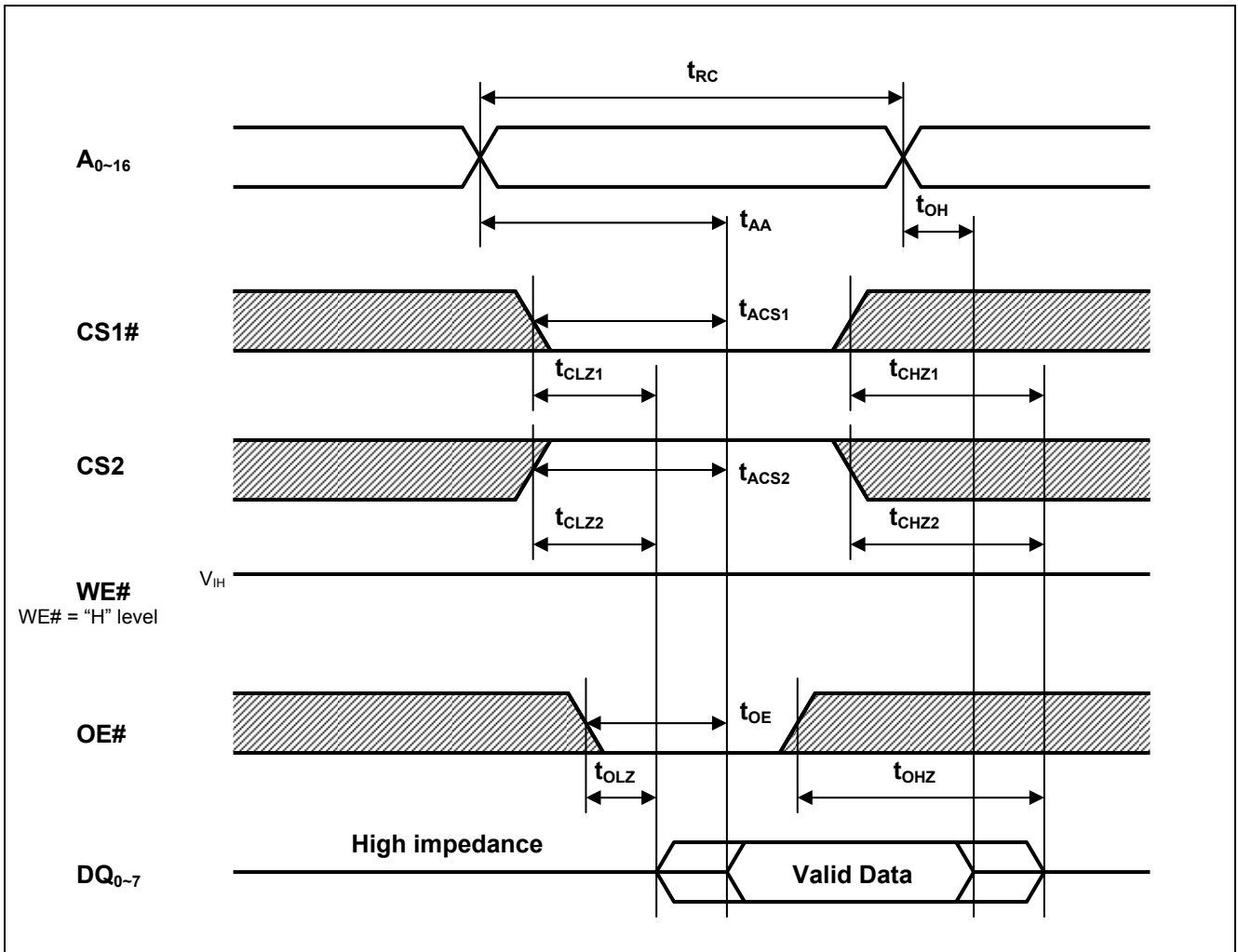
Write Cycle

Parameter	Symbol	R1LV0108E**-5**		R1LV0108E**-7**		Unit	Note
		Min.	Max.	Min.	Max.		
Write cycle time	t_{WC}	55	-	70	-	ns	
Address valid to end of write	t_{AW}	50	-	55	-	ns	
Chip select to end of write	t_{CW}	50	-	55	-	ns	5
Write pulse width	t_{WP}	45	-	50	-	ns	4
Address setup time	t_{AS}	0	-	0	-	ns	6
Write recovery time	t_{WR}	0	-	0	-	ns	7
Data to write time overlap	t_{DW}	25	-	30	-	ns	
Data hold from write time	t_{DH}	0	-	0	-	ns	
Output enable from end of write	t_{OW}	5	-	5	-	ns	2
Output disable to output in high-Z	t_{OHZ}	0	20	0	25	ns	1,2
Write to output in high-Z	t_{WHZ}	0	20	0	25	ns	1,2

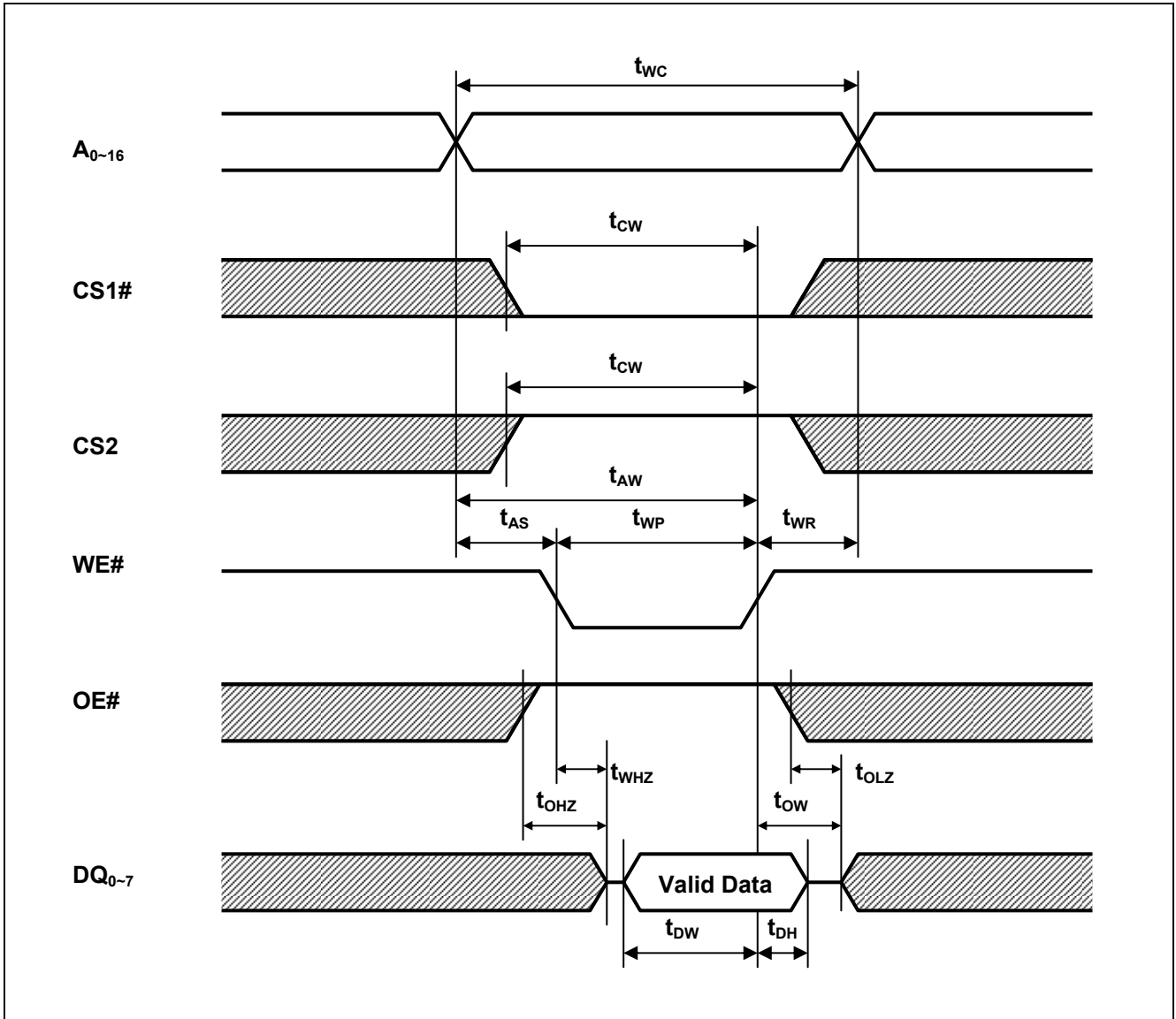
- Note
- t_{CHZ} , t_{OHZ} and t_{WHZ} are defined as the time at which the outputs achieve the open circuit conditions and are not referred to output voltage levels.
 - This parameter is sampled and not 100% tested.
 - At any given temperature and voltage condition, t_{tHZ} max is less than t_{tLZ} min both for a given device and from device to device.
 - A write occurs during the overlap of a low CS1#, a high CS2, a low WE#.
A write begins at the latest transition among CS1# going low, CS2 going high and WE# going low.
A write ends at the earliest transition among CS1# going high, CS2 going low and WE# going high.
 t_{WP} is measured from the beginning of write to the end of write.
 - t_{CW} is measured from the later of CS1# going low or CS2 going high to end of write.
 - t_{AS} is measured the address valid to the beginning of write.
 - t_{WR} is measured from the earliest of CS1# or WE# going high or CS2 going low to the end of write cycle.
 - Don't apply inverted phase signal externally when DQ pin is output mode.

Timing Waveforms

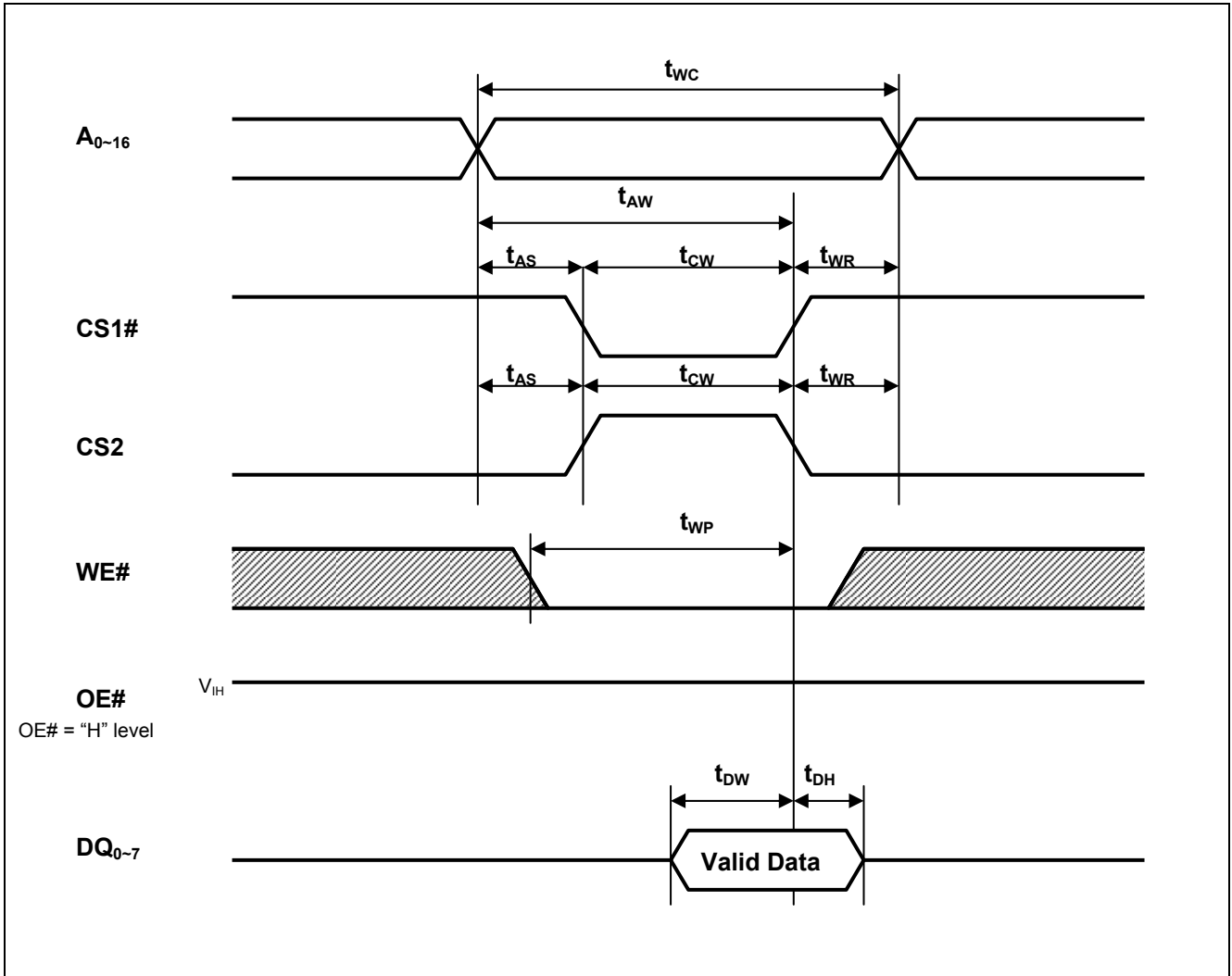
Read Cycle



Write Cycle (1) (WE# CLOCK)



Write Cycle (2) (CS1#, CS2 CLOCK)

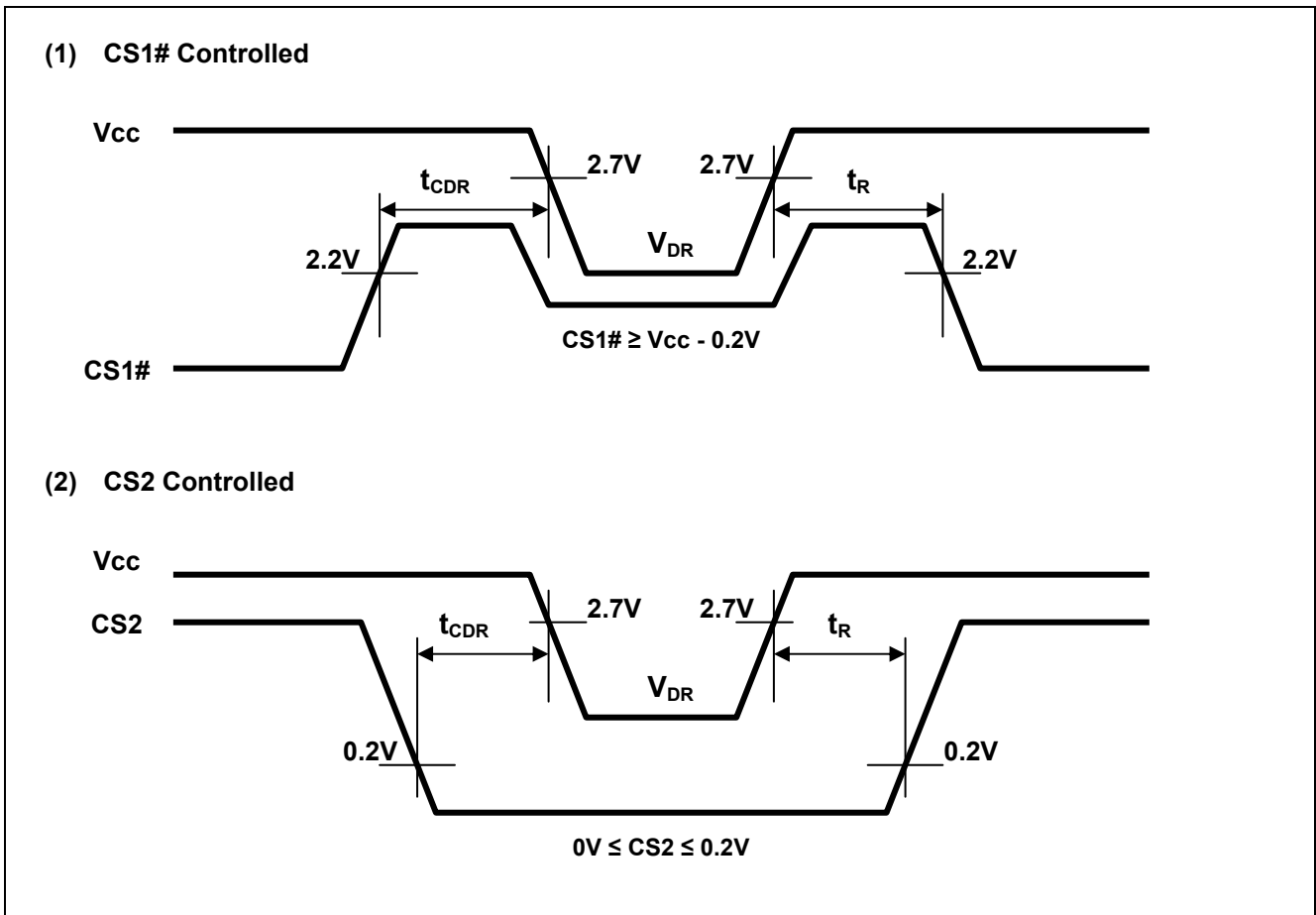


Low Vcc Data Retention Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test conditions ²	
V _{CC} for data retention	V _{DR}	2.0	-	3.6	V	V _{in} ≥ 0V (1) 0V ≤ CS2 ≤ 0.2V or (2) CS1# ≥ V _{CC} -0.2V, CS2 ≥ V _{CC} -0.2V	
Data retention current	I _{CCDR}	-	0.6 ^{*1}	2	μA	~+25°C	V _{CC} =3.0V, V _{in} ≥ 0V (1) 0V ≤ CS2 ≤ 0.2V or (2) CS1# ≥ V _{CC} -0.2V, CS2 ≥ V _{CC} -0.2V
		-	-	3	μA	~+40°C	
		-	-	8	μA	~+70°C	
		-	-	10	μA	~+85°C	
Chip deselect to data retention time	t _{CDR}	0	-	-	ns	See retention waveform.	
Operation recovery time	t _R	5	-	-	ms		

Note 1. Typical parameter indicates the value for the center of distribution at 3.0V (T_a= 25°C), and not 100% tested.
 2. CS2 controls address buffer, WE# buffer, CS1# buffer, OE# buffer and Din buffer. If CS2 controls data retention mode, V_{in} levels (address, WE#, CS1#, OE#, DQ) can be in the high impedance state.
 If CS1# controls data retention mode, CS2 must be CS2 ≥ V_{CC}-0.2V or 0V ≤ CS2 ≤ 0.2V. The other input levels (address, WE#, OE#, DQ) can be in the high impedance state.

Low Vcc Data Retention Timing Waveforms



Revision History	R1LV0108E Series Data Sheet
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Rev.	Date	Description	
		Page	Summary
1.00	2013.6.21	-	First Edition issued

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Renesas Electronics America Inc.
2880 Scott Boulevard Santa Clara, CA 95050-2554, U.S.A.
Tel: +1-408-588-6000, Fax: +1-408-588-6130

Renesas Electronics Canada Limited
1101 Nicholson Road, Newmarket, Ontario L3Y 9C3, Canada
Tel: +1-905-898-5441, Fax: +1-905-898-3220

Renesas Electronics Europe Limited
Dukes Meadow, Millboard Road, Bourne End, Buckinghamshire, SL8 5FH, U.K.
Tel: +44-1628-651-700, Fax: +44-1628-651-804

Renesas Electronics Europe GmbH
Arcadiastrasse 10, 40472 Düsseldorf, Germany
Tel: +49-211-65030, Fax: +49-211-6503-1327

Renesas Electronics (China) Co., Ltd.
7th Floor, Quantum Plaza, No.27 ZhiChunLu Haidian District, Beijing 100083, P.R.China
Tel: +86-10-8235-1155, Fax: +86-10-8235-7679

Renesas Electronics (Shanghai) Co., Ltd.
Unit 204, 205, AZIA Center, No.1233 Lujiazui Ring Rd., Pudong District, Shanghai 200120, China
Tel: +86-21-5877-1818, Fax: +86-21-6887-7858 / -7898

Renesas Electronics Hong Kong Limited
Unit 1601-1613, 16/F., Tower 2, Grand Century Place, 193 Prince Edward Road West, Mongkok, Kowloon, Hong Kong
Tel: +852-2886-9318, Fax: +852 2886-9022/9044

Renesas Electronics Taiwan Co., Ltd.
13F, No. 363, Fu Shing North Road, Taipei, Taiwan
Tel: +886-2-8175-9600, Fax: +886 2-8175-9670

Renesas Electronics Singapore Pte. Ltd.
80 Bendemeer Road, Unit #06-02 Hyflux Innovation Centre Singapore 339949
Tel: +65-6213-0200, Fax: +65-6213-0300

Renesas Electronics Malaysia Sdn.Bhd.
Unit 906, Block B, Menara Amcorp, Amcorp Trade Centre, No. 18, Jln Persiaran Barat, 46050 Petaling Jaya, Selangor Darul Ehsan, Malaysia
Tel: +60-3-7955-3390, Fax: +60-3-7955-9510

Renesas Electronics Korea Co., Ltd.
11F., Samik Laviel' or Bldg., 720-2 Yeoksam-Dong, Kangnam-Ku, Seoul 135-080, Korea
Tel: +82-2-558-3737, Fax: +82-2-558-5141